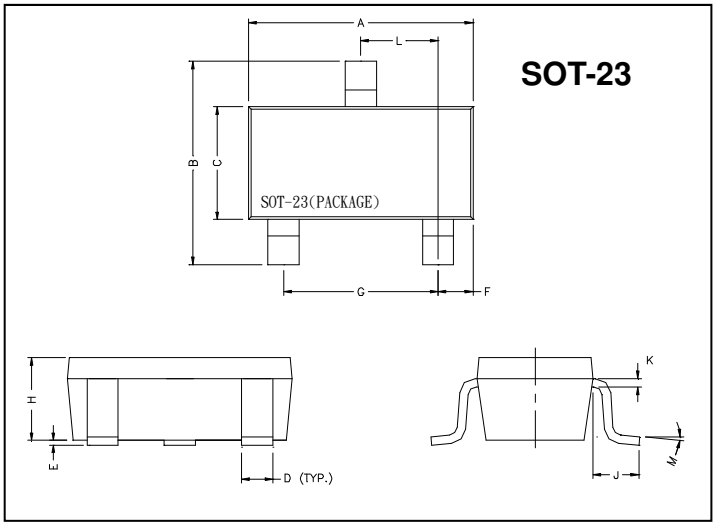
GMBT5401

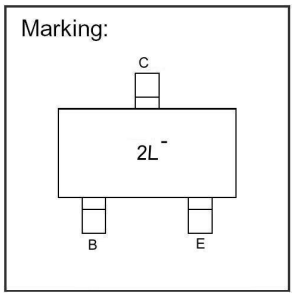
PNP EPITAXIAL PLANAR TRANSISTOR

Description

The GMBT5401 is designer for general purpose applications requiring high breakdown voltages.

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

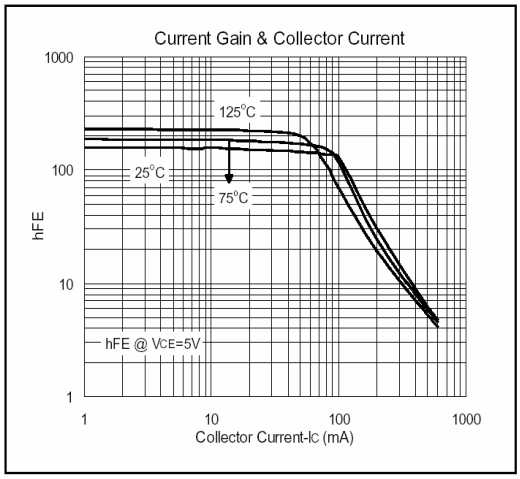
Absolute Maximum Ratings at Ta = 25℃

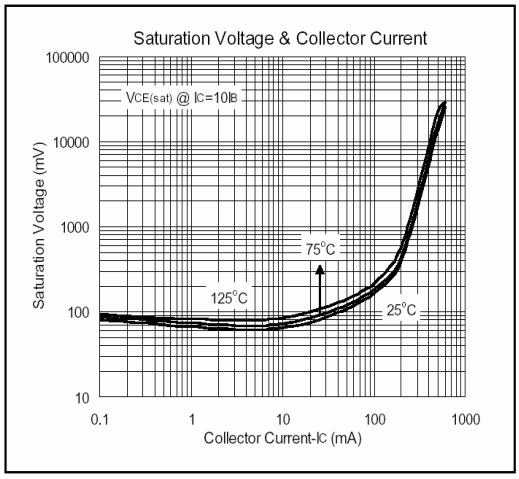
Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55 ~ +150	℃
Collector to Base Voltage	V_{CBO}	-160	V
Collector to Emitter Voltage	V_{CEO}	-150	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-600	mA
Total Power Dissipation	P_D	225	mW

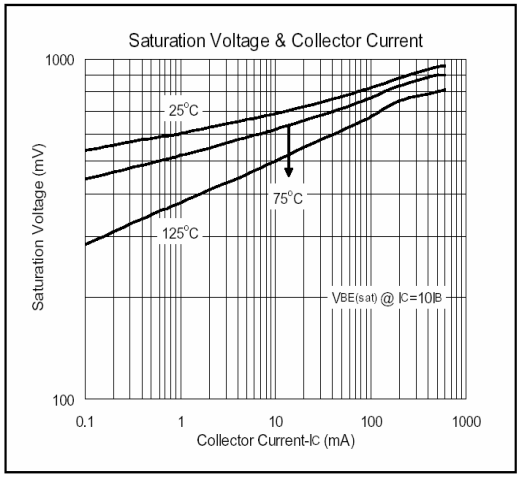
Characteristics at Ta = 25℃

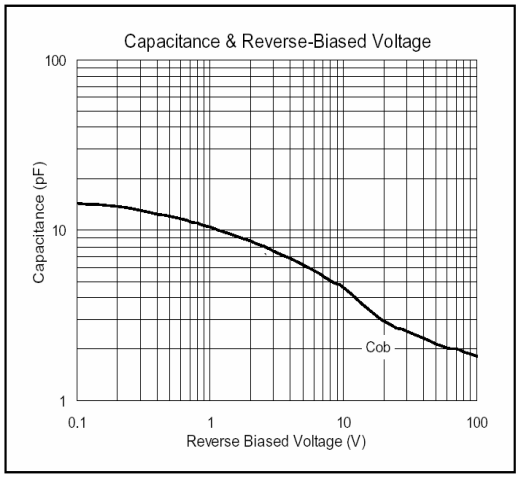
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	-160	-	-	V	I_C=-100uA, I_E =0
BV_{CEO}	-150	-	-	V	I_C=-1mA, I_B=0
BV_{EBO}	-5	-	-	V	I_E=-10uA, I_C=0
I_{CBO}	-	-	-50	nA	V_{CB}=-120V , I_E=0
$V_{CE(sat)1}$	-	-	-200	mV	I_C=-10mA, I_B= -1mA
$V_{CE(sat)2}$	-	-	-500	mV	I_C=-50mA, I_B= -5mA
$V_{BE(sat)1}$	-	-	-1	V	I_C=-10mA, I_B= -1mA
$V_{BE(sat)2}$	-	-	-1	V	I_C=-50mA, I_B= -5mA
hFE1	50	-	-		V_{CE}=-5V, I_C= -1mA
hFE2	60	-	240		V_{CE}=-5V, I_C= -10mA
hFE3	50	-	-		V_{CE}=-5V, I_C= -50mA
fT	100	-	300	MHz	V_{CE}=-10V, I_C= -10mA, f=100MHz
Cob	-	-	6	pF	V_{CB}=-10V, f=1MHz

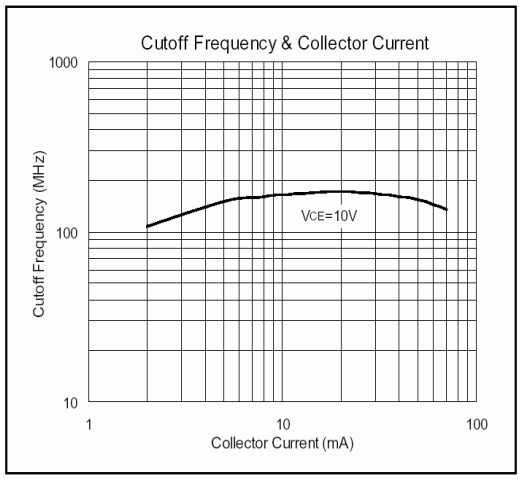
Characteristics Curve











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